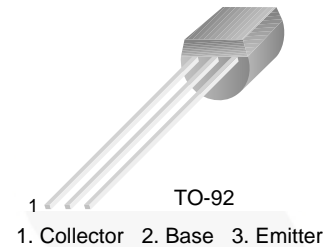




BC546 / BC547 / BC548 / BC549 / BC550 NPN Epitaxial Silicon Transistor

Features

- Switching and Amplifier
- High-Voltage: BC546, $V_{CEO} = 65\text{ V}$
- Low-Noise: BC549, BC550
- Complement to BC556, BC557, BC558, BC559, and BC560



Ordering Information

Part Number	Marking	Package	Packing Method
BC546ABU	BC546A	TO-92 3L	Bulk
BC546ATA	BC546A	TO-92 3L	Ammo
BC546BTA	BC546B	TO-92 3L	Ammo
BC546BTF	BC546B	TO-92 3L	Tape and Reel
BC546CTA	BC546C	TO-92 3L	Ammo
BC547ATA	BC547A	TO-92 3L	Ammo
BC547B	BC547B	TO-92 3L	Bulk
BC547BBU	BC547B	TO-92 3L	Bulk
BC547BTA	BC547B	TO-92 3L	Ammo
BC547BTF	BC547B	TO-92 3L	Tape and Reel
BC547CBU	BC547C	TO-92 3L	Bulk
BC547CTA	BC547C	TO-92 3L	Ammo
BC547CTFR	BC547C	TO-92 3L	Tape and Reel
BC548BU	BC548	TO-92 3L	Bulk
BC548BTA	BC548B	TO-92 3L	Ammo
BC548CTA	BC548C	TO-92 3L	Ammo
BC549BTA	BC549B	TO-92 3L	Ammo
BC549BTF	BC549B	TO-92 3L	Tape and Reel
BC549CTA	BC549C	TO-92 3L	Ammo
BC550CBU	BC550C	TO-92 3L	Bulk
BC550CTA	BC550C	TO-92 3L	Ammo

BC546 / BC547 / BC548 / BC549 / BC550 — NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit	
V_{CBO}	Collector-Base Voltage	BC546	80	V
		BC547 / BC550	50	
		BC548 / BC549	30	
V_{CEO}	Collector-Emitter Voltage	BC546	65	V
		BC547 / BC550	45	
		BC548 / BC549	30	
V_{EBO}	Emitter-Base Voltage	BC546 / BC547	6	V
		BC548 / BC549 / BC550	5	
I_C	Collector Current (DC)	100	mA	
P_C	Collector Power Dissipation	500	mW	
T_J	Junction Temperature	150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-65 to +150	$^\circ\text{C}$	

Electrical Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-Off Current	$V_{CB} = 30\text{ V}, I_E = 0$			15	nA
h_{FE}	DC Current Gain	$V_{CE} = 5\text{ V}, I_C = 2\text{ mA}$	110		800	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10\text{ mA}, I_B = 0.5\text{ mA}$		90	250	mV
		$I_C = 100\text{ mA}, I_B = 5\text{ mA}$		250	600	
$V_{BE(sat)}$	Collector-Base Saturation Voltage	$I_C = 10\text{ mA}, I_B = 0.5\text{ mA}$		700		mV
		$I_C = 100\text{ mA}, I_B = 5\text{ mA}$		900		
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 5\text{ V}, I_C = 2\text{ mA}$	580	660	700	mV
		$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}$			720	
f_T	Current Gain Bandwidth Product	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}, f = 100\text{ MHz}$		300		MHz
C_{ob}	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$		3.5	6.0	pF
C_{ib}	Input Capacitance	$V_{EB} = 0.5\text{ V}, I_C = 0, f = 1\text{ MHz}$		9		pF
NF	Noise Figure	BC546 / BC547 / BC548	$V_{CE} = 5\text{ V}, I_C = 200\text{ }\mu\text{A}, f = 1\text{ kHz}, R_G = 2\text{ k}\Omega$	2	10	dB
		BC549 / BC550		1.2	4.0	
		BC549	$V_{CE} = 5\text{ V}, I_C = 200\text{ }\mu\text{A}, R_G = 2\text{ k}\Omega, f = 30\text{ to }15000\text{ MHz}$	1.4	4.0	
		BC550		1.4	3.0	

h_{FE} Classification

Classification	A	B	C
h_{FE}	110 ~ 220	200 ~ 450	420 ~ 800

Typical Performance Characteristics

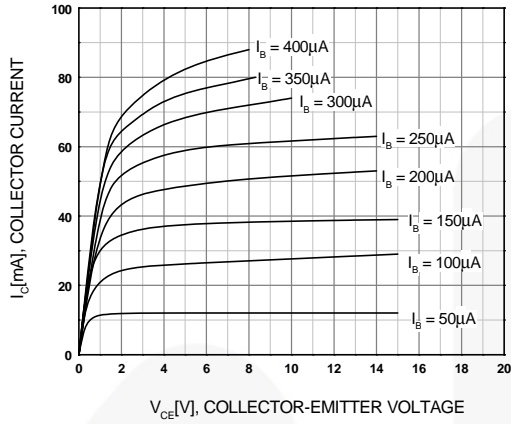


Figure 1. Static Characteristic

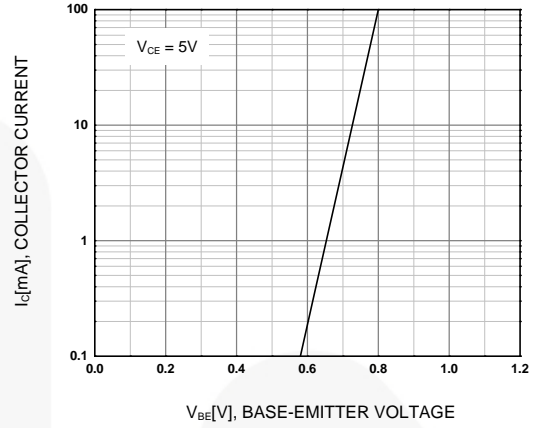


Figure 2. Transfer Characteristic

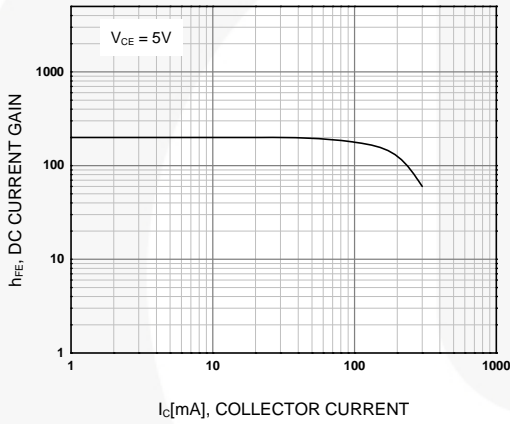


Figure 3. DC Current Gain

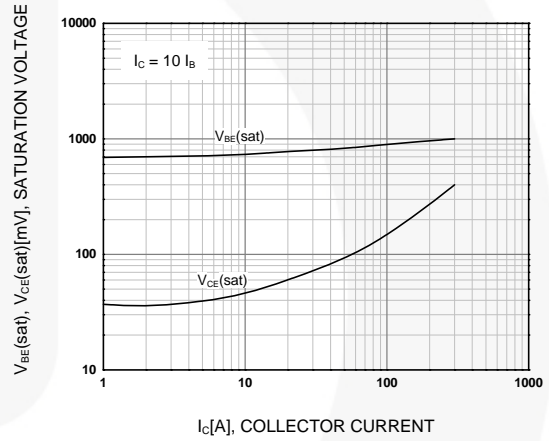


Figure 4. Base-Emitter Saturation Voltage and Collector-Emitter Saturation Voltage

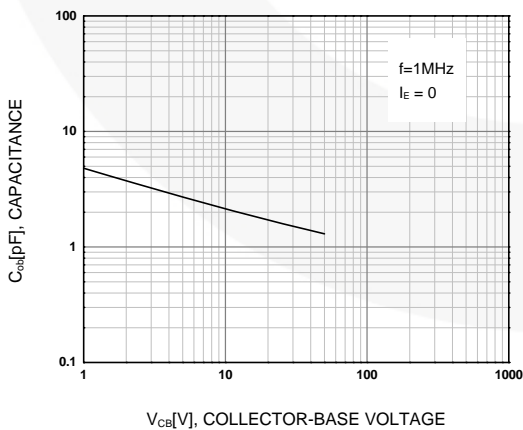


Figure 5. Output Capacitance

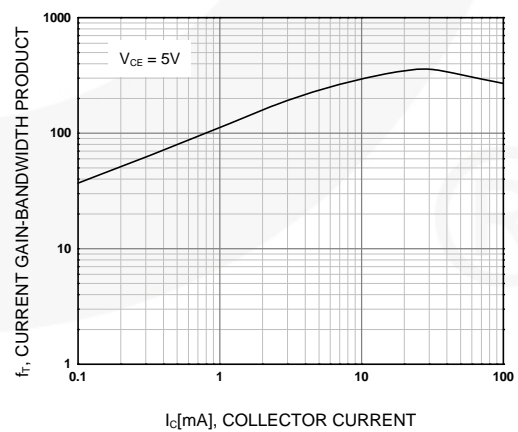


Figure 6. Current Gain Bandwidth Product

Physical Dimensions

TO-92 (Bulk)

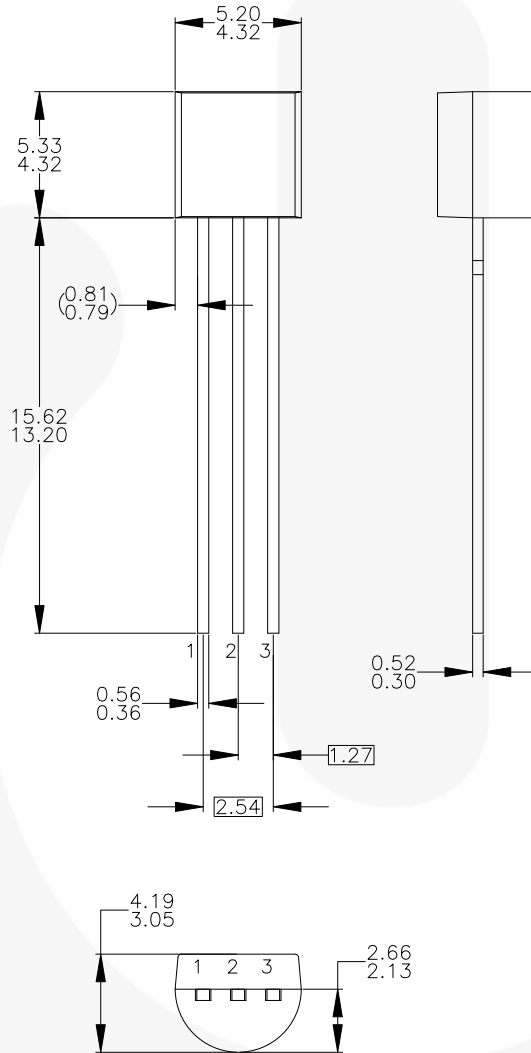


Figure 7. 3-LEAD, TO92, JEDEC TO-92 COMPLIANT STRAIGHT LEAD CONFIGURATION (OLD TO92AM3)

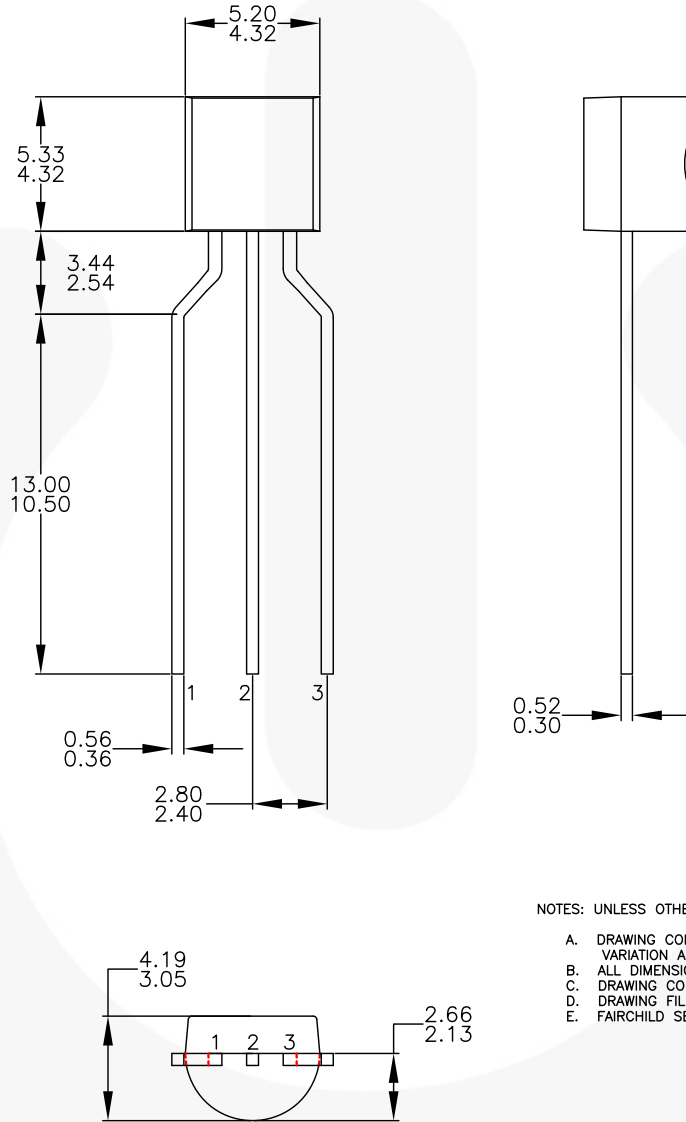
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Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:
<http://www.fairchildsemi.com/dwg/ZA/ZA03D.pdf>.

For current tape and reel specifications, visit Fairchild Semiconductor's online packaging area:
http://www.fairchildsemi.com/packag_dwg/PKG-ZA03D_BK.pdf.

Physical Dimensions (Continued)

TO-92 (Ammo, Tape and Reel)



NOTES: UNLESS OTHERWISE SPECIFIED

- A. DRAWING CONFORMS TO JEDEC MS-013, VARIATION AC.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5M-2009.
- D. DRAWING FILENAME: MKT-ZA03FREV3.
- E. FAIRCHILD SEMICONDUCTOR.

Figure 8. 3-LEAD, TO92, MOLDED 0.200 IN LINE SPACING LEAD FORM (J61Z OPTION)

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